AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (original) An alkoxide compound represented by
general formula (I):

$$\mathbf{N} = \left(-0 - \mathbf{C} - \mathbf{A} - \mathbf{N} \right)_{\mathbf{R}^4}$$
 (1)

wherein one of R^1 and R^2 represents an alkyl group having 1 to 4 carbon atoms, and the other represents a hydrogen atom or an alkyl group having 1 to 4 carbon atoms; R^3 and R^4 each represent an alkyl group having 1 to 4 carbon atoms; A represents an alkanediyl group having 1 to 8 carbon atoms; M represents a silicon atom or a hafnium atom; and n represents 4.

- (original) The alkoxide compound according to claim
 wherein A in general formula (I) is a methylene group.
- 3. (previously presented) The alkoxide compound according to claim 1, wherein M in general formula (I) is a silicon atom.

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- 4. (previously presented) The alkoxide metal compound according to claim 1, wherein M in general formula (I) is a hafnium atom.
- 5. (previously presented) A material for thin film formation comprising the alkoxide compound according to claim 1.
 - 6. (canceled)
- 7. (previously presented) The alkoxide compound according to claim 2, wherein M in general formula (I) is a silicon atom.
- 8. (previously presented) The alkoxide metal compound according to claim 4, wherein M in general formula (I) is a hafnium atom.
- 9. (previously presented) A material for thin film formation comprising the alkoxide compound according to claim 2.
- 10. (previously presented) A material for thin film formation comprising the alkoxide compound according to claim 3.
- 11. (previously presented) A material for thin film formation comprising the alkoxide compound according to claim 4.

12-14. (canceled)